N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 60V
- I_D 300mA
- $R_{DS(ON)}$(at V_{GS}=10V) 2.0ohm
- $R_{DS(ON)}$(at V_{GS}=4.5V) 2.5ohm
- ESD protected up to 2.0KV (HBM)

General Description

- Trench Power MV MOSFET technology

■ Typical Performance Characteristics

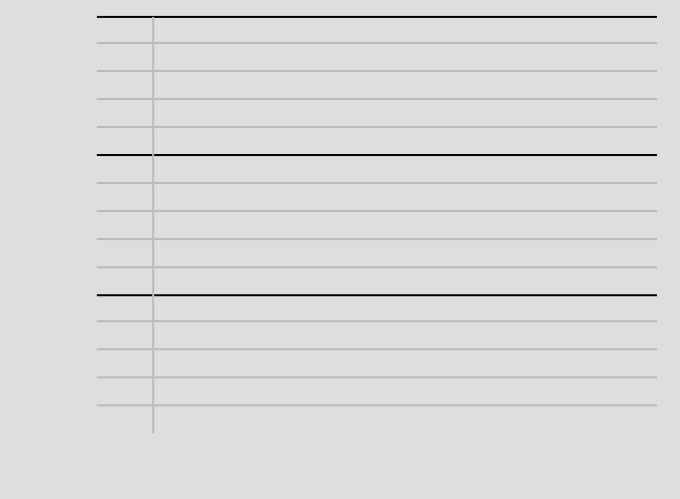

Figure1. Output Characteristics

Figure2. Transfer Characteristics

Figure3. Capacitance Characteristics

Figure4. Gate Charge

Figure5. On-Resistance vs Gate to Source Voltage

Figure6. Normalized On-Resistance

Figure 7. $R_{DS(on)}$ VS Drain Current

Figure 8. Forward characteristics of reverse diode

Figure 9. Normalized breakdown voltage

Figure 10. Normalized Threshold voltage

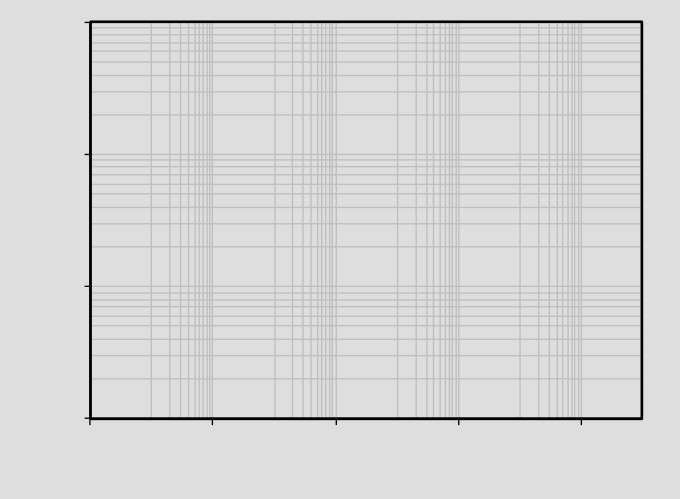

Figure 11. Maximum Transient Thermal Impedance

Figure 12. Safe Operation Area

■ Test Circuits & Waveforms

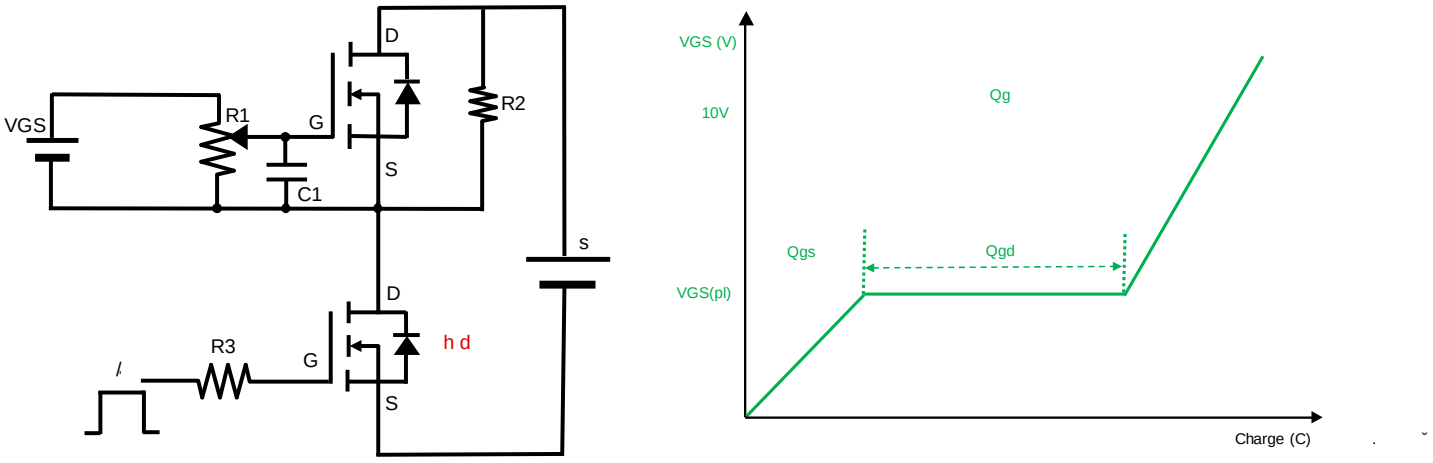

Figure A. Gate Charge Test Circuit & Waveform

Figure B. Resistive Switching Test Circuit & Waveform

Figure C. Diode Recovery Test Circuit & Waveform

■ SOT-323 Package Outline Dimensions

■ Marking Information

72KD$_p$

Note:
1. All marking is at middle of the product body
2. All marking is in laser marking
3. 72KD is Marking Code
4. Body color: Black

Disclaimer

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